M62420SP/ FP/ AFP

2ch Electronic Volume with Tone by I²C Bus System

REJ03F0051-0100Z
Rev.1.0
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Description

M62420SP/FP/AFP is the tone and volume controller which is controlled by I²C bus. This IC can apply the broad application because of low noise and distortion.
M62420AFP changes the slave address from M62420FP.

Features

- TONE(Bass/Treble) control and 1 dB step volume control are enabled.
- Low noise and low distortion .
  V_{NO} = 4.5 µVrms, CTHD=0.1% max
- Controlling by serial data in conformity to the I²C bus format .

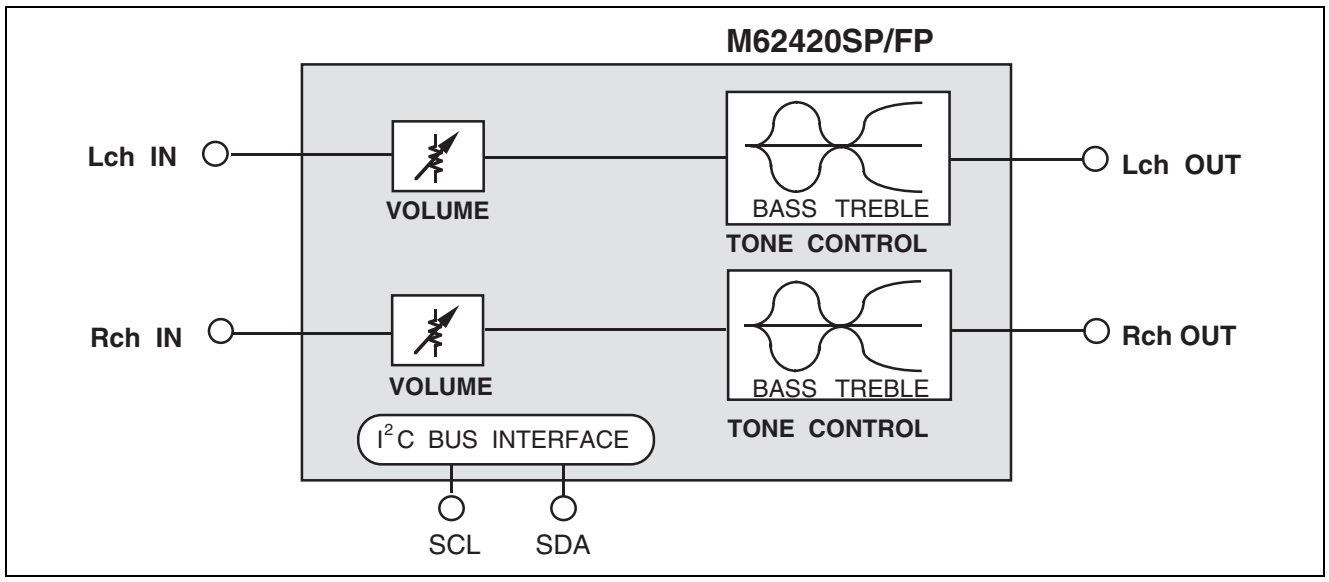
Applications

- TV, Mini-Stereo, etc

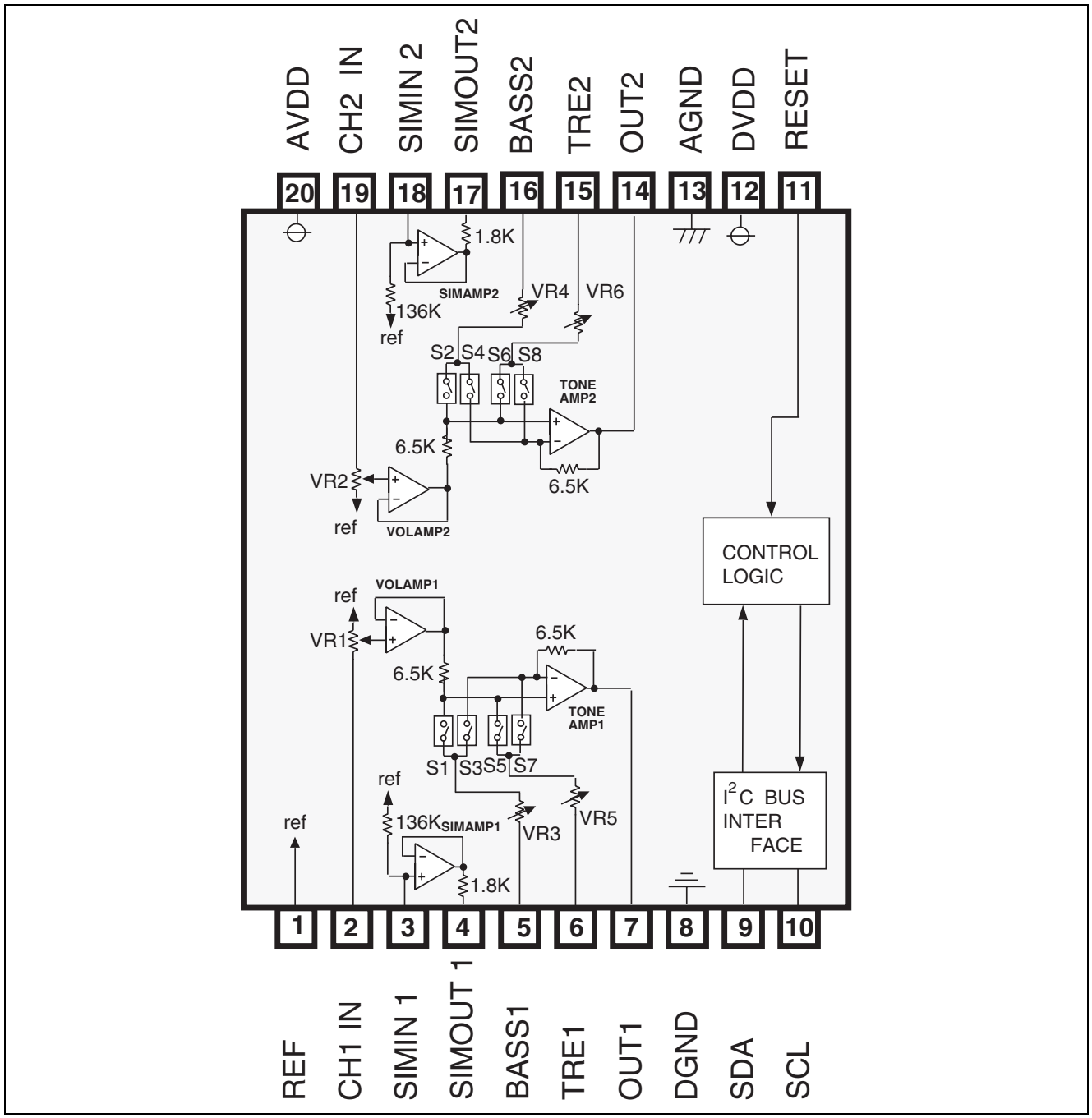
Recommended Operating Condition

- Supply voltage range: 8.5 to 9.5 V (analog) 4.5 to 5.5 V (digital)
- Rated supply voltage: 9 V (analog) 5 V (digital)

System Block Diagram



Block diagram and Pin Configuration



Pin Description

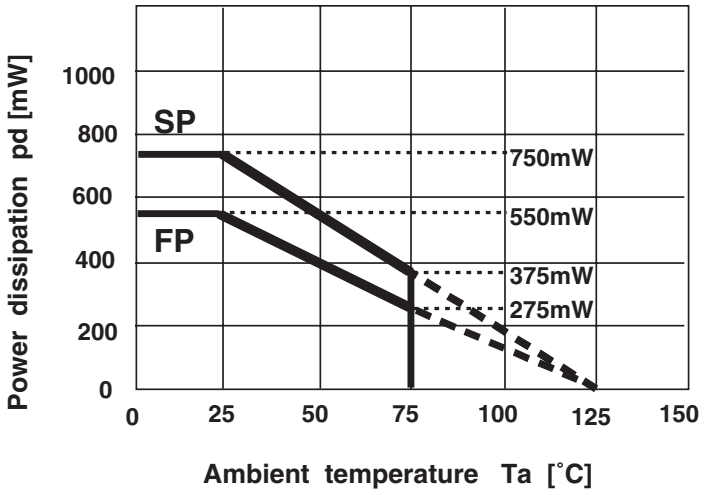
Pin No.	Pin Name	I/O	Description
1	REF	I	Reference voltage terminal for analog
2	CH1 IN	I	Input terminal (ch1)
3	SIMIN1	I	Pin for capacitor of simulated inductor 1
4	SIMOUT 1	O	Pin for capacitor of simulated inductor 1
5	BASS1	I	Pin for capacitor of ch1-side bass setting
6	TRE1	I	Pin for capacitor of ch1-side treble setting
7	VOL OUT1	O	Output terminal (ch1)
8	DGND	I	Digital GND
9	SDA	I/O	I/O terminal of DATA I^2C bus format
10	SCL	I	Input terminal of CLOCK I^2C bus format
11	RESET	I	RESET terminal of built-in logic circuit
12	DVDD	I	VDD for digital circuit
13	AGND	I	GND for analog circuit
14	VOL OUT2	O	Output terminal (ch2)
15	TRE2	I	Pin for capacitor of ch2-side treble setting
16	BASS2	I	Pin for capacitor of ch2-side bass setting
17	SIMOUT2	O	Pin for capacitor of simulated inductor 2
18	SIMIN 2	I	Pin for capacitor of simulated inductor 2
19	CH2 IN	I	Input terminal (ch2)
20	AVDD	I	VCC for analog circuit

Absolute Maximum Ratings

(Ta = 25°C)

Symbol	Parameter	Condition	Limits	Unit
AVdd	Analog supply voltage		10.0	V
DVdd	Digital supply voltage		7.0	V
Pd	Power dissipation	Ta ≤ 25°C	750	mW
Kθ	Thermal Derating ratio	Ta > 25°C	7.5	mW / °C
Topr	Operating temperature		–20 to +75	°C
Tstg	Storage temperature		–40 to +125	°C

Thermal Derating Curves



Recommended Operating Condition

(Ta = 25°C unless otherwise noted)

Item	Symbol	Condition	MIN	TYP	MAX	Unit
Analog supply voltage	AVDD		8.5	9.0	9.5	V
Digital supply voltage	DVDD		4.5	5.0	5.5	V
H level input voltage (logic circuit)	VIH		0.7DVDD	—	VDD	V
H level input voltage (logic circuit)	VIL		0	—	0.3DVDD	V

Electrical Characteristics (DC)

(Ta = 25°C, AVDD = 9 V, DVDD = 5 V and tone, bassboost = 0 dB unless otherwise noted)

(1) Supply voltage

Item	Symbol	Conditions	Limit			Unit
			Min.	Typ.	Max.	
Analog supply current	Icc	AVdd = 9.0 V Measure terminal = 20 pin No signal input	—	10	20	mA
Digital supply current	Idd	DVdd = 5 V Measure terminal = 12 pin No signal input	–	0	2	µA

(2) I/O CHARACTERISTICS

Item	Symbol	Conditions	Limit			Unit
			Min.	Typ.	Max.	
Maximum input voltage	VIM	2,19 pin input, 7,14 pin output RL = 10 K, THD = 1%, f = 1 kHz ATT = -6dB	2.0	3.2	—	Vrms
Output voltage	Vodc	7 pin, 14 pin, no signal	4.35	4.5	4.65	V
Gain	Gv	Vin = 0dBm, FLAT, f = 1 kHz 2-7PIN 19-14PIN gain	–2	0	2	dB
Output noise voltage	Vono	JIS-A filter, no signal, Rg =10 KΩ 7,14 pin	—	4.5	30	µVrms
Total harmonic distortion	THD	7 pin, 14 pin f=1kHz Vo = 0.5 Vrms, RL = 10KΩ LPF = 30 kHz	—	0.05	0.1	%
Channel separation	CT	RL = 10 K S:Vin = 1 Vrms,f=1kHz M:Rg = 10 kΩ, JIS-A filter	—	–100	–70	dB

(3) Tone Characteristics

Item	Symbol	Conditions	Limit			Unit
			Min.	Typ.	Max.	
Tone control gain (bass)	Gbassb	f = 100 Hz	9	12	15	dB
	Gbassc		–15	–12	–9	dB
Tone control gain (treble)	Gtrebb	f = 10 Hz	9	12	15	dB
	Gtrebc		–15	–12	–9	dB

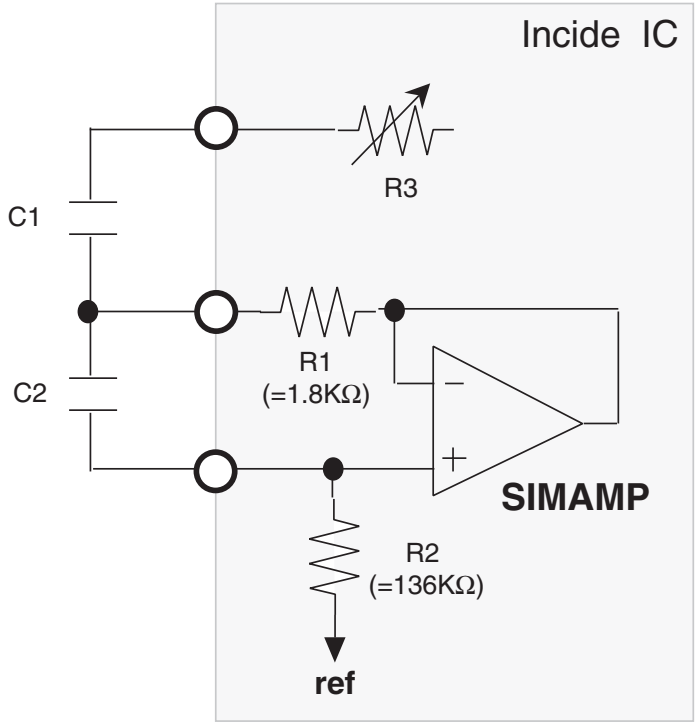
(4) Volume Characteristics

Item	Symbol	Conditions	Limit			Unit
			Min.	Typ.	Max.	
Maximum attenuation	ATTmax	f = 1KHz, Vin = 0dBm 2 pin to 7 pin 19 pin to 14pin gain JIS-A filter	–108	–100	–80	dB
Minimum attenuation	ATTmin		–1.5	0	1.5	dB

Function Explanation

(1) Equivaration Circuit of Tone Control

The resonance circuit is able to construct by using built-in amplifier for simulated inductor. (Shows the constant as follow)



Center frequency

$$f0 = 1 / 2\pi\sqrt{C1 \bullet C2 \bullet R1 \bullet R2}\ [Hz]$$

$$Q = \sqrt{(C2 \bullet R2) / (C1 \bullet R1)}$$

(EX) BASS band (f=100Hz)
R1=1.8KΩ , R2=136KΩ
C1=0.47μF , C2=0.022μF

FIG1. The circuit used simurated inductor.

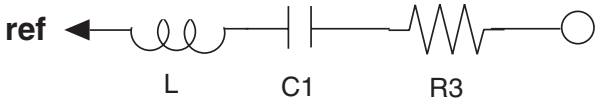
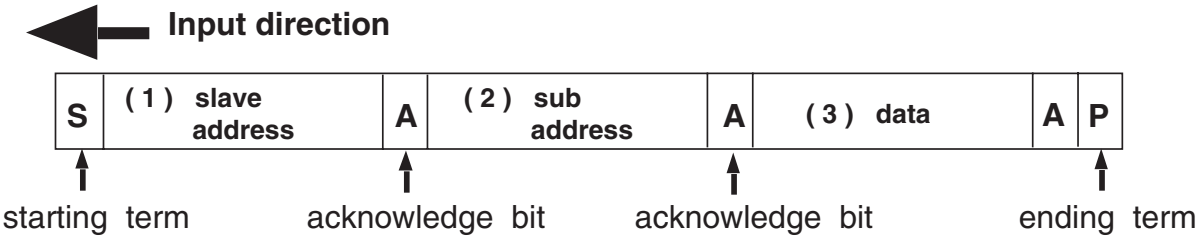


FIG2. The equivalent circuit used L.

FIG1 is equal to FIG2.
The following relation is concluded.

$$L = C2 \bullet ER1 \bullet ER2$$

I²C BUS Input Data Format



(1) Slave address

M62420SP / FP

A6	A5	A4	A3	A2	A1	A0	R/W
1	0	0	0	0	0	0	0

M62420AFP

A6	A5	A4	A3	A2	A1	A0	R/W
1	0	0	0	0	0	1	0

(2) sub address

The following sub address is defined at this IC.

subA7	subA6	subA5	subA4	subA3	subA2	subA1	subA0
empty slot			MUTE mode 1: ON 0: OFF	TREBLE level mode 1: ON 0: OFF	BASS level mode 1: ON 0: OFF	channel2 volume mode 1: ON 0: OFF	channel1 volume mode 1: ON 0: OFF

(3) -1: volume control

The volume control is enabled at following condition.

subA0 : 0, 1, 1
subA1 : 1, 0, 1 (either bit is 1)

subA2 : 0
subA3 : 0 (both bits are 0)

volume code

ATT	D4	D3	D2	D1	D0
0dB	H	H	H	H	H
2dB	H	H	H	H	L
4dB	H	H	H	L	H
6dB	H	H	H	L	L
8dB	H	H	L	H	H
10dB	H	H	L	H	L
12dB	H	H	L	L	H
14dB	H	H	L	L	L
16dB	H	L	H	H	H
18dB	H	L	H	H	L
20dB	H	L	H	L	H
22dB	H	L	H	L	L
24dB	H	L	L	H	H
26dB	H	L	L	H	L
28dB	H	L	L	L	H
30dB	H	L	L	L	L
32dB	L	H	H	H	H
34dB	L	H	H	H	L
36dB	L	H	H	L	H
38dB	L	H	H	L	L
40dB	L	H	L	H	H
42dB	L	H	L	H	L
46dB	L	H	L	L	H
50dB	L	H	L	L	L
54dB	L	L	H	H	H
58dB	L	L	H	H	L
62dB	L	L	H	L	H
66dB	L	L	H	L	L
70dB	L	L	L	H	H
74dB	L	L	L	H	L
78dB	L	L	L	L	H
∞dB	L	L	L	L	L

ATT	D6	D5
0dB	H	H
1dB	H	L
* 2dB	L	H
* 3dB	L	L

* 2dB,3dB setting is enabled at less than 42dB step.

(3) -2 : tone level control

The tone level controlling is enabled at following condition.

subA0 : 0
subA1 : 0 (both bits are 0)

subA2 : 0 , 1 , 1
subA3 : 1 , 0 , 1 (either bit is 1)

tone code

	BASS				TREBLE			
	D7	D6	D5	D4	D3	D2	D1	D0
12dB	L	H	H	L	L	H	H	L
10dB	L	H	L	H	L	H	L	H
8dB	L	H	L	L	L	H	L	L
6dB	L	L	H	H	L	L	H	H
4dB	L	L	H	L	L	L	H	L
2dB	L	L	L	H	L	L	L	H
0dB	L	L	L	L	L	L	L	L
-2dB	H	L	L	H	H	L	L	H
-4dB	H	L	H	L	H	L	H	L
-6dB	H	L	H	H	H	L	H	H
-8dB	H	H	L	L	H	H	L	L
-10dB	H	H	L	H	H	H	L	H
-12dB	H	H	H	L	H	H	H	L

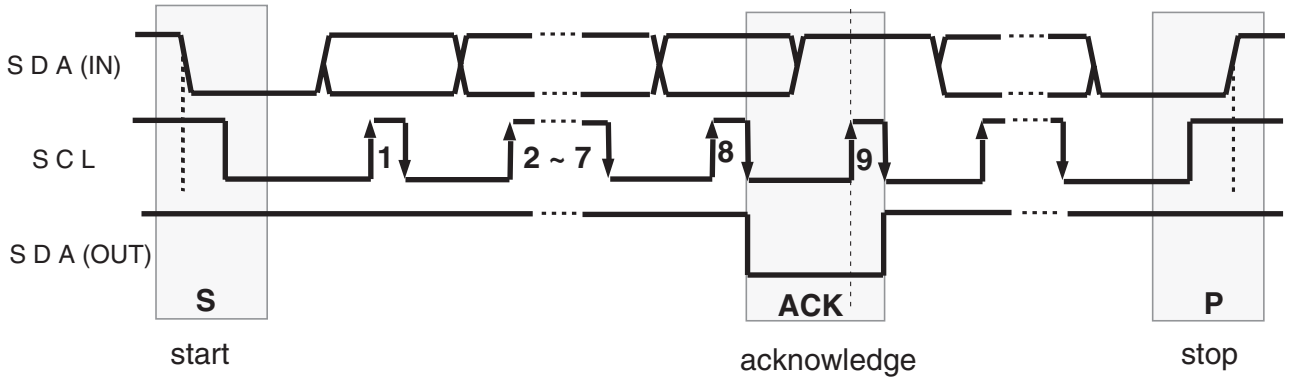
non-used code HHHH
LHHH
HLLL

(3) -3 : Mute mode

The mute mode is enabled at following condition.

subA0 : no definition
subA1 : no definition
subA2 : no definition
subA3 : no definition
subA4 : 1

DATA and CLOCK



start

This term is defined by SDA(in) falling edge at SCL H .

stop

This term is defined by SDA(in) rising edge at SCL H .

CAUTION

The SDA(IN) level never change at SCK=H except start and stop .

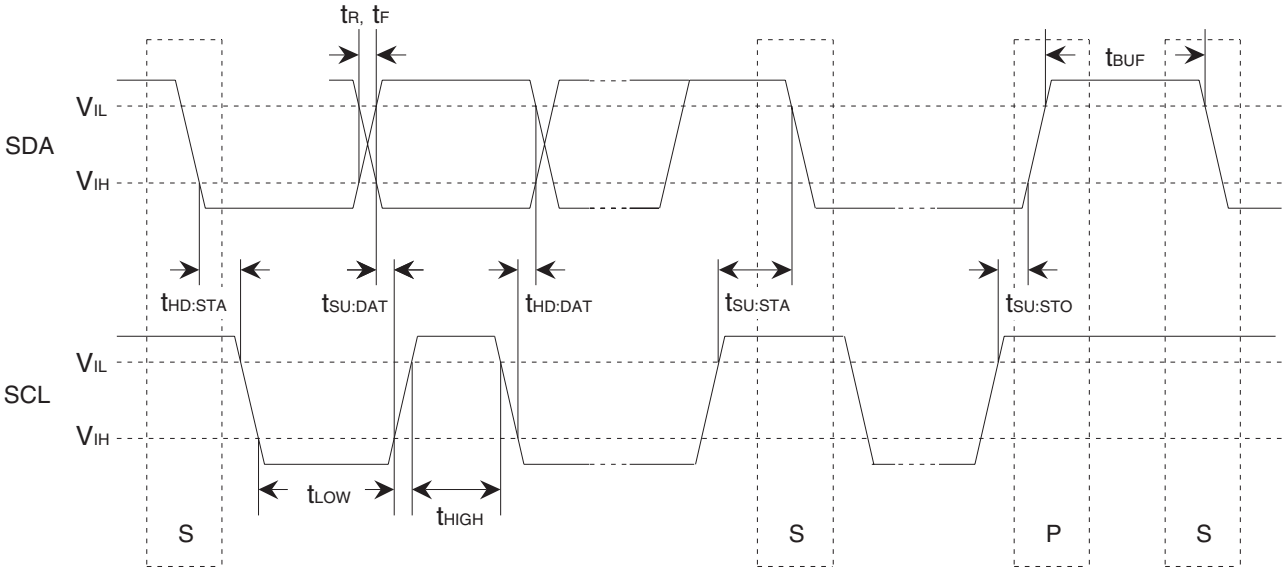
data transmisson

The SDA(IN) is enabled at SCL rising edge and H .

acknowledge

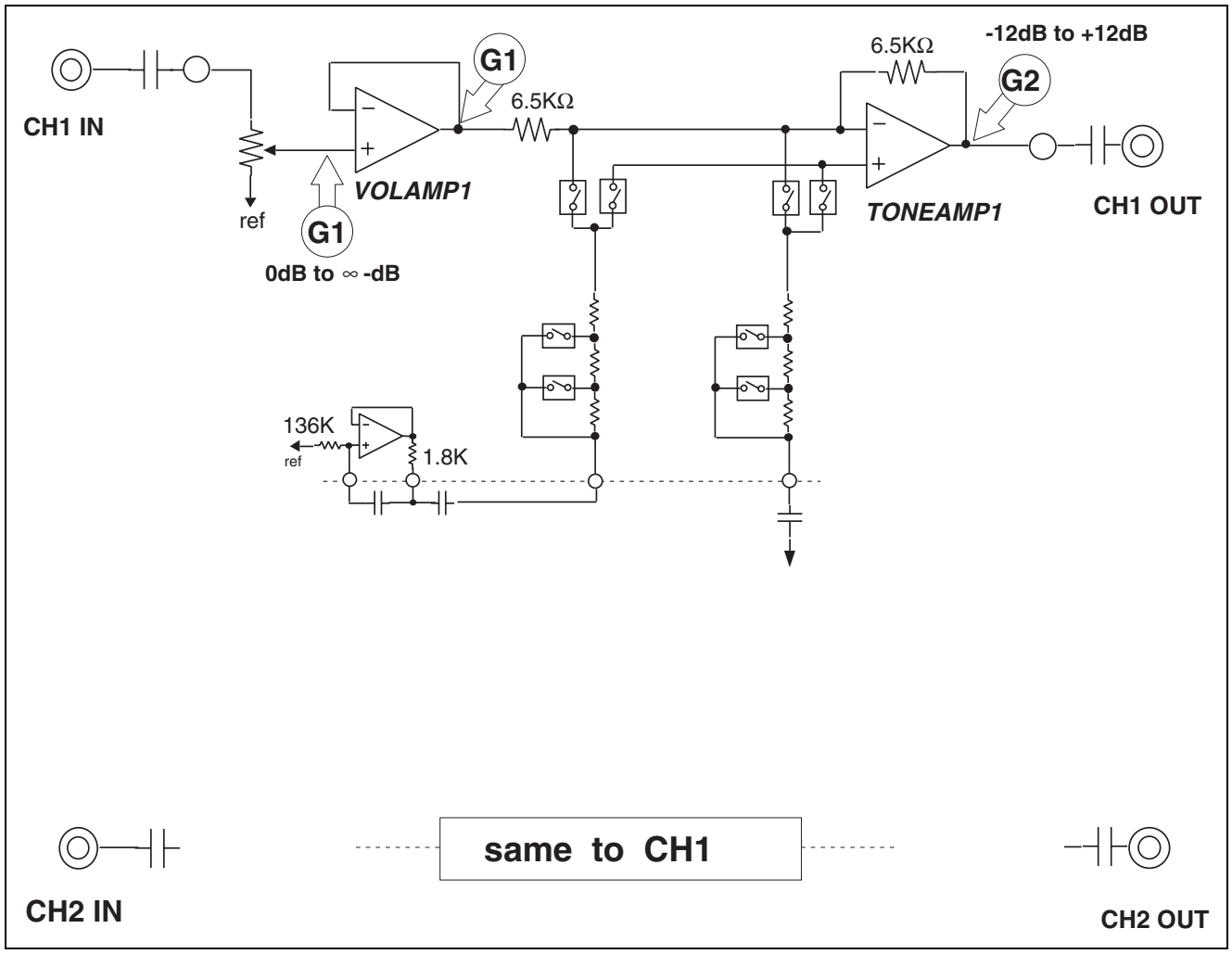
Transmitter must send H during ninth clock pulse of SCL .
The case of finished receiving , the receiver replies L synchronized to falling edge of eighth pulse . And restart receiving the transmitted data synchronized to falling edge of ninth pulse .

BUS Line Timing Specification

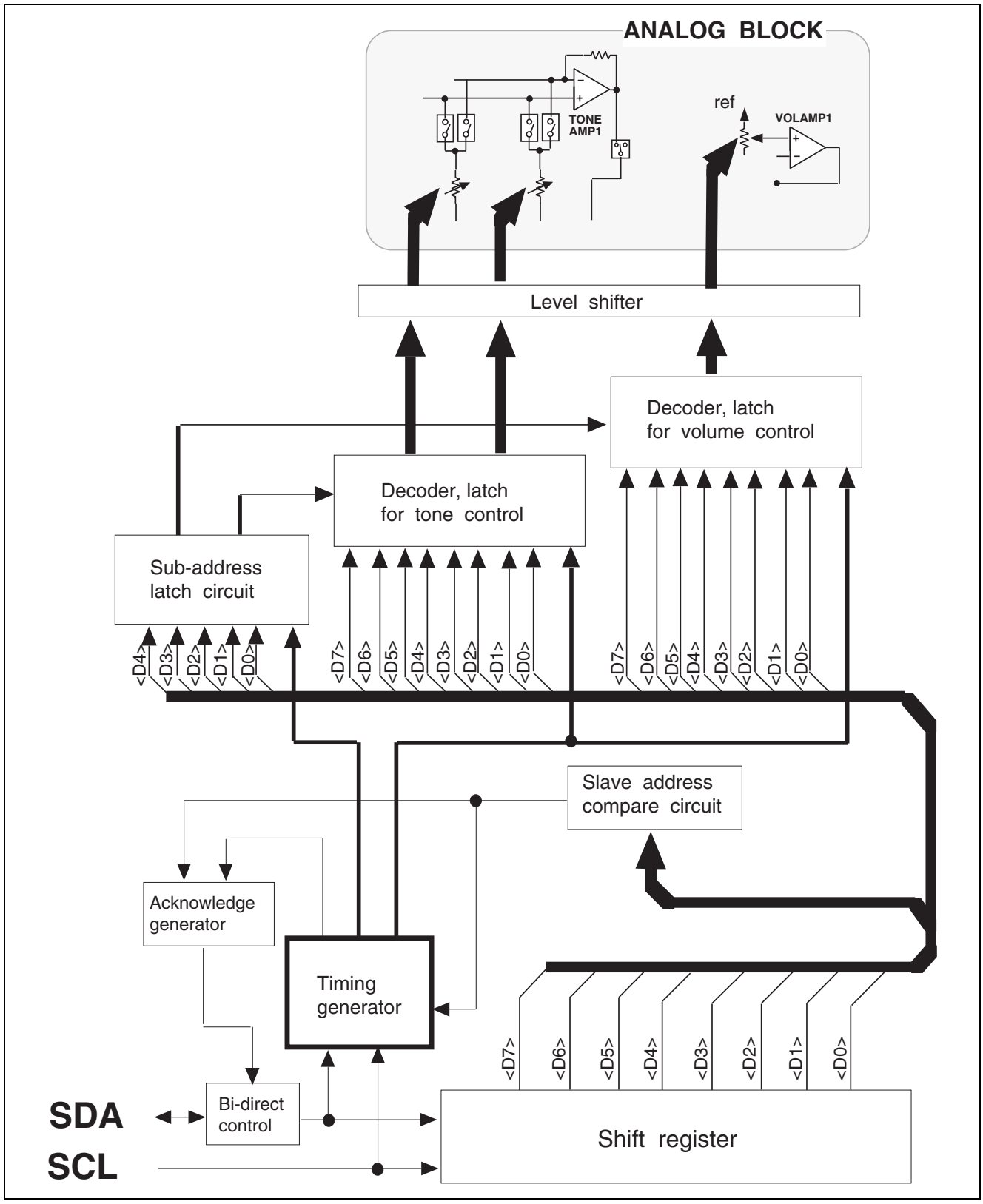


Parameter	Symbol	MIN	MAX	Units
Min. input low voltage	V_{IL}	–0.5	1.5	V
Max. input high voltage	V_{IH}	3.0	5.5	V
SCL clock frequency	f_{SCL}	0	100	kHz
Time the bus must be free before a new transmission can start	t_{BUF}	4.7		µs
Hold time start condition. After this period the first clock pulse is generated	$t_{HD:STA}$	4.0		µs
The LOW period of the clock	t_{LOW}	4.7		µs
The HIGH period of the clock	t_{HIGH}	4.0		µs
Set up time for start condition (Only relevant for a repeated start condition)	$t_{SU:STA}$	4.7		µs
Hold time DATA	$t_{HD:DAT}$	0		µs
Set-up time DATA	$t_{SU:DAT}$	250		ns
Rise time of both SDA and SCL lines	t_R		1000	ns
Fall time of both SDA and SCL lines	t_F		300	ns
Set-up time for stop condition	$t_{SU:STO}$	4.0		µs

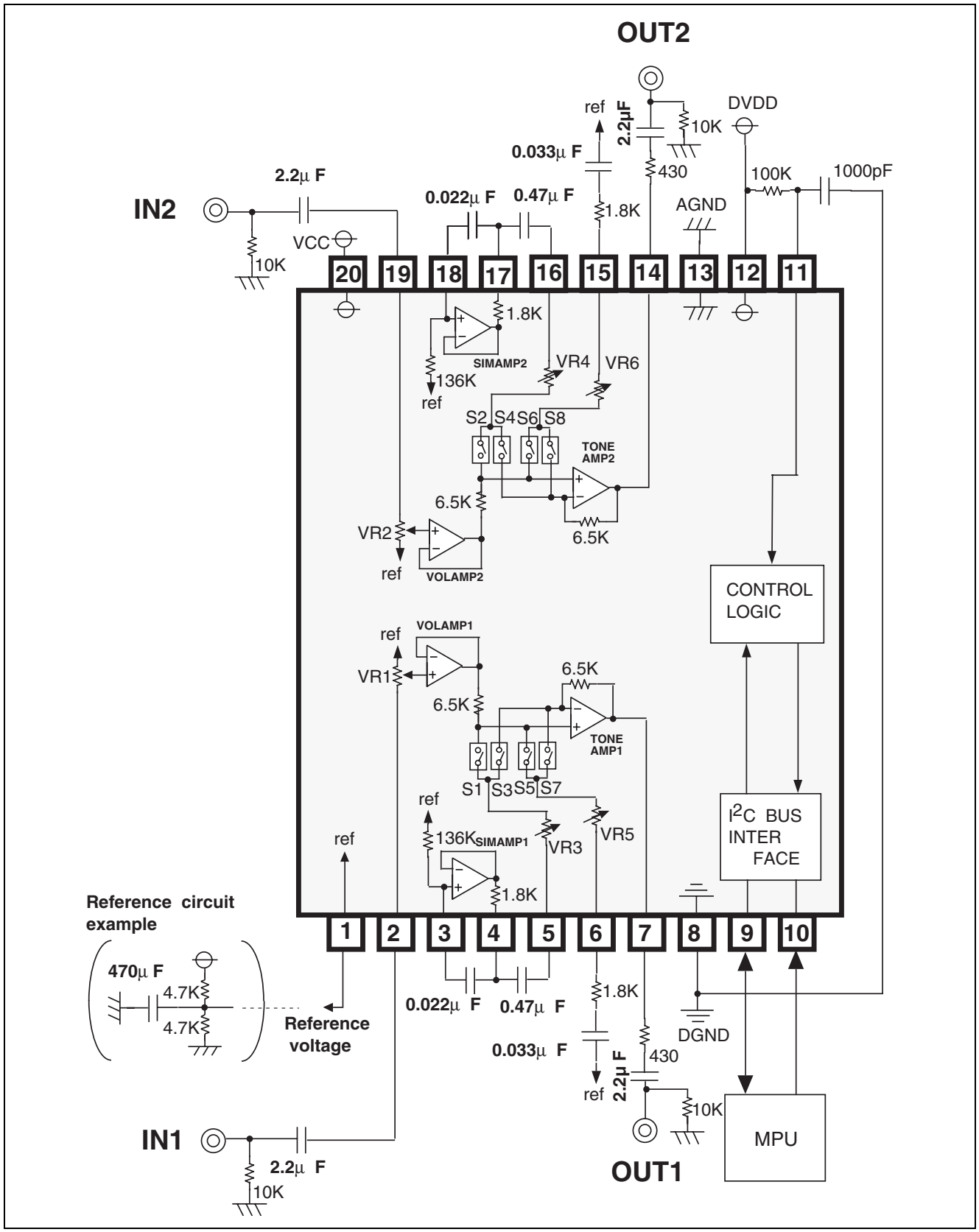
Level Diagram



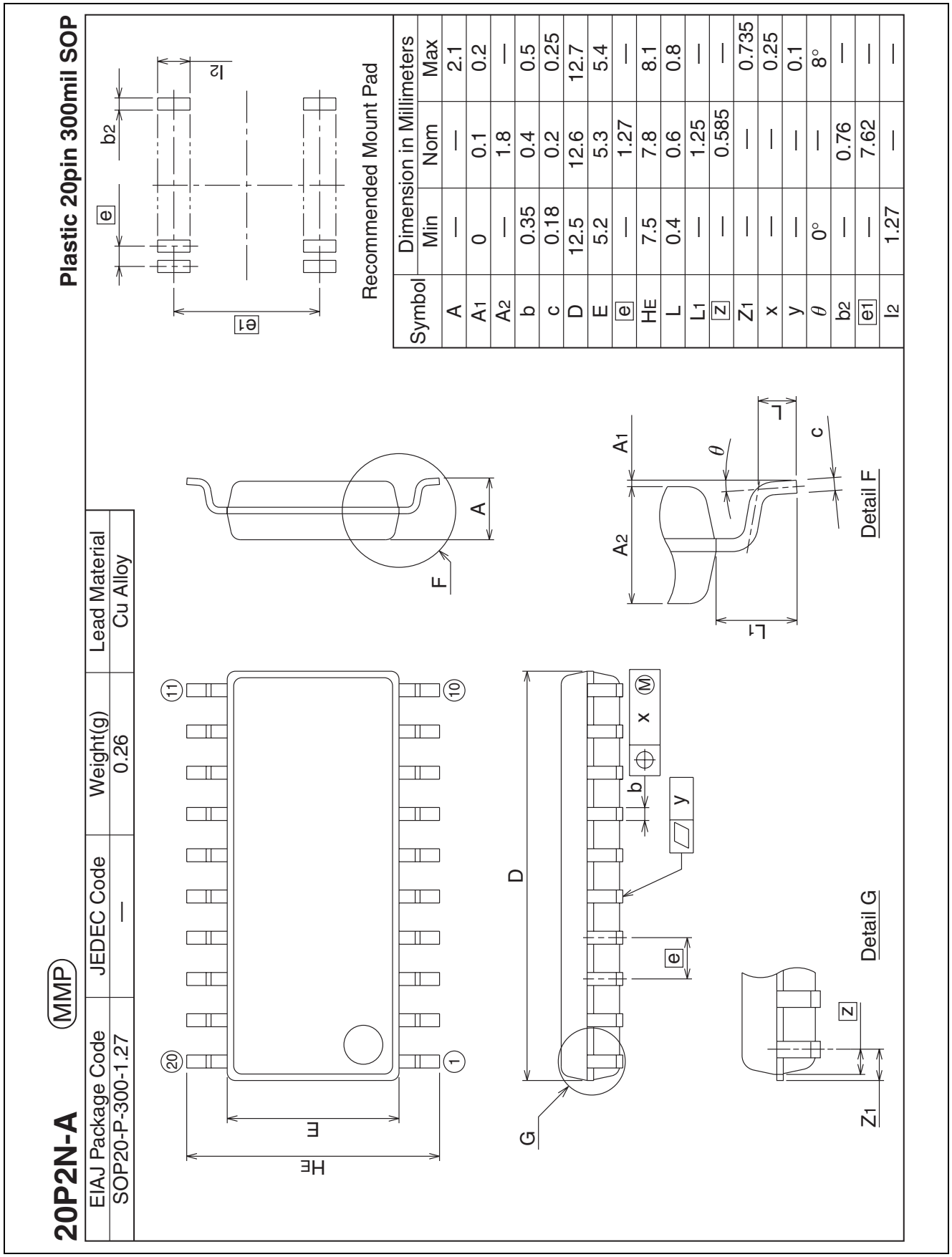
Logic Circuit



Application Example



Package Dimensions



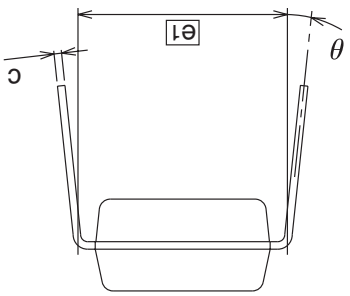
20P4B

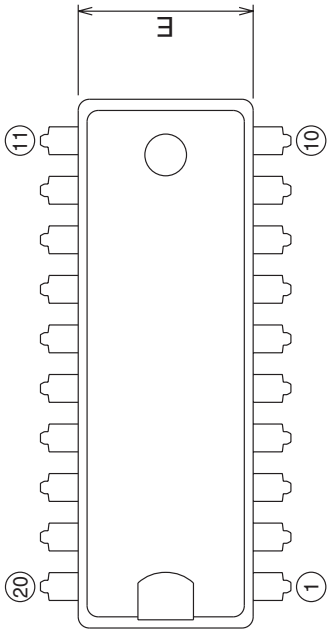
MMP

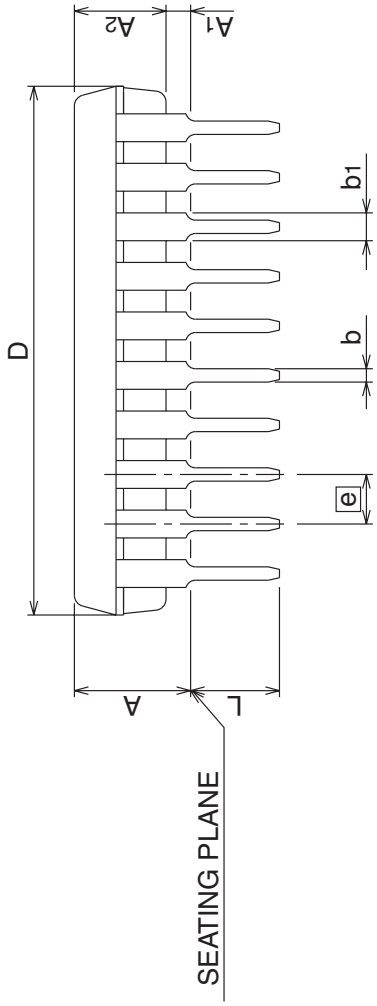
Plastic 20pin 300mil SDIP

EIAJ Package Code	JEDEC Code	Weight(g)	Lead Material
SDIP20-P-300-1.78	—	1.0	Alloy 42/Cu Alloy

Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	—	—	4.5
A_1	0.51	—	—
A_2	—	3.3	—
b	0.38	0.48	0.58
b_1	0.9	1.0	1.3
c	0.22	0.27	0.34
D	18.8	19.0	19.2
E	6.15	6.3	6.45
e	—	1.778	—
e1	—	7.62	—
L	3.0	—	—
θ	0°	—	15°







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